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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Hussein I. Hanafi, et al. Docket: 15949

Patent No: 7,018,873 Dated: June 20, 2006

Issued: March 28, 2006

**For: METHOD OF MAKING A DEVICE THRESHOLD
CONTROL OF FRONT-GATE SILICON-ON-INSULATOR
MOSFET USING A SELF-ALIGNED BACK-GATE**

**Commissioner of Patents
P.O. Box 1450
Alexandria, VA 22313-1450**

REQUEST FOR CERTIFICATE OF CORRECTION

Sir:

**It appearing that errors have been introduced in the course
of printing the Patent issued in the above application, it is respectfully
requested that the Commissioner issue a Certificate of Correction in
the following respects:**

**57) Abstract
“provides SOI CMOS”**

should read

--The present invention provides SOI CMOS--

*Certificate
JUN 26 2006
of Correction*

Column 11, Line 19, Claim 17:
“forming suicide” should read -- forming silicide --

Column 12, Line 20, Claim 19:
“polySi gates and the” should read -- polySi gate and the --

Respectfully submitted,



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**UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION**

PATENT NO : **7,018,873**

APPLICATION NO : **10/639,942**

ISSUE DATE : **March 28, 2006**

INVENTOR(S) : **Hussein I. Hanafi, et al.**

It is certified that an error appears or errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

57) Abstract
"provides SOI CMOS"

should read

--The present invention provides SOI CMOS --

Column 11, Line 19, Claim 17:
"forming suicide" should read -- forming silicide --

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"polySi gates and the" should read -- polySi gate and the --

MAILING ADDRESS OF SENDER:

PATENT No. **7,018,873**

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